

Jack C. Lee

Professor and Cullen Trust for Higher Education Endowed Professorship in
Engineering # 4, Electrical and Computer Engineering Department
The University of Texas at Austin

Research / teaching experience and expertise:

- Integrated circuits manufacturing
- Photovoltaic/solar cell technologies
- Alternative channel devices
- Dielectric and passivation processes
- Display technologies
- Semiconductor memory devices

Education

9/84 – 8/88 Ph.D., Electrical Engineering, University of California at Berkeley
9/80 – 12/81 M.S., Electrical Engineering, University of California at Los Angeles
9/76 – 6/80 B.S., Electrical Engineering (with highest honors),
University of California at Los Angeles

Professional Career

9/00 – present Cullen Trust for Higher Education Endowed Professorship in Engineering #4
Department of Electrical and Computer Engineering
The University of Texas at Austin
9/96 – present Professor, Department of Electrical and Computer Engineering
The University of Texas at Austin
9/92 – 8/96 Assistant Professor, Department of Electrical and Computer Engineering
The University of Texas at Austin
9/88 – 8/92 Associate Professor, Department of Electrical and Computer Engineering
The University of Texas at Austin
1/88 – 6/88 Lecturer, Electrical Engineering and Computer Science Department
University of California at Berkeley
6/79 – 8/84 Member of Technical Staff, High-Speed Bipolar Device Program
TRW Microelectronics Center, Redondo Beach, CA

Honors and Awards

IEEE Electron Devices Society Distinguished Lecturer, 2004 - 2016.
Fellow, The Institute of Electrical and Electronic Engineers (IEEE), 2002 “For
contributions to the understanding and development of ultra-thin dielectrics and their
application to silicon devices”
Gordon Lepley IV Endowed Memorial Teaching Award, ECE Department, The
University of Texas at Austin, 2004
Cullen Trust For Higher Education Endowed Professorship in Engineering, 2000-present
Dean’s Fellow, College of Engineering, The University of Texas at Austin, 1999, 2003
Lockheed Fort-Worth Division Award for Excellence in Engineering Teaching,
College of Engineering, The University of Texas at Austin, 1996
Award of Excellence, Halliburton Foundation, 1993
Departmental Teaching Award, College of Engineering, The University of Texas at
Austin, 1993
SRC Inventor Recognition Award, Semiconductor Research Corporation, 1991

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Hughes Aircraft Company Endowed Faculty Fellowship in Engineering,
The University of Texas at Austin, 1991- 2000
Outstanding Engineering Teaching by an Assistant Professor, College of Engineering,
The University of Texas at Austin, 1991
Best Paper Award, SEMATECH Centers of Excellence Coordination Meeting, 1990.
Dow Outstanding Young Faculty Award, American Society for Engineering Education,
1990
Engineering Research Initiation Award, Engineering Foundation of the United
Engineering Trustees, 1989
Best Paper Award, IEEE International Reliability Physics Symposium, 1988

Litigation Experience as Testifying Experts

The following is a list of cases in which I have provided testimony, at trial, deposition, or a tutorial.

- Greenthread LLC v. Samsung
February 2020 –
(Representing plaintiff, Greenthread LLC)
- Impinj, Inc. v. NXP USA, Inc.
September 2019 –
(Representing defendant, NXP USA, Inc.)
- MLC Intellectual Property LLC vs. Micron Technology, Inc.,
June 2016 –
(Representing plaintiff, MLC Intellectual Property LLC)
- Hanwha v. LONGi Solar Technology
April 2019 – June 2020
(Representing defendant LONGi Solar Technology)
- Vista Peak Ventures, LLC v. Innolux Corp.
January 2019 – March 2019
(Representing IPR Petitioner, Innolux Corp.)
- Home Semiconductor Corp. v. Samsung
August 2018 – June 2020
(Representing plaintiff, Home Semiconductor Corp.)
- Macronix v. Toshiba
May 2017 – February 2018
(Representing defendant, Toshiba)
- University of Illinois v. Micron Technology
September 2009 – November 2017
(Representing plaintiff, Univ. of Illinois)

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- Godo Kaisha IP Bridge 1 v. OmniVision Technologies, Inc.
January 2018 – December 2018
(Representing defendant, OmniVision Technologies, Inc.)
- Silicon Genesis v. Soitec
October 2016 – March 2017
(Representing plaintiff, Silicon Genesis)
- Samsung Electronics v. NVIDIA Corporation,
January 2015 – April 2016
(Representing defendant, NVIDIA)
- Macronix, Inc. v. Spansion, Inc.
September 2014 – January 2015
(Representing defendant, Spansion, Inc.)
- Keranos, LLC v. MicrochipTechnology, Inc.
August 2012 – February 2014
(Representing defendant, MicrochipTechnology)
- Elpida Memory, Inc. vs. Nanya Technology Corporation
April 2012 – December 2012
(Representing defendant, Nanya Technology Corporation)
- Spansion LLC v. Samsung
July 2009 – March 2010
(Representing plaintiff, Spansion LLC)
- Advanced Micro Devices v. Samsung
March 2008 – September 2010
(Representing plaintiff, Advanced Micro Devices)
- Agere Systems Inc. v. Rohm Co. Ltd.
April 2006 – November 2007
(Representing plaintiff, Agere Systems Inc.)

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Publications

Refereed Journal Publications

1. J. Lee, K. Mayaram and C. Hu, "A Theoretical Study of Gate/Drain Offset in LDD MOSFET's," IEEE Electron Device Letters, vol. EDL-7, no. 3, p. 152 - 154, March 1986.
2. J. Lee, I-C Chen and C. Hu, "Comparison Between CVD and Thermal Oxide Dielectric Integrity," IEEE Electron Device Letters, vol. EDL-7, no. 9, p. 506 - 509, September 1986.
3. K. Mayaram, J. Lee and C. Hu, "A Model for the Electric Field in Lightly Doped Drain Structures," IEEE Transactions on Electron Devices, vol. ED-34, no.7, p. 1509 - 1518, July 1987.
4. J. Lee and C. Hu, "Polarity Asymmetry of Oxides Grown on Polycrystalline Silicon," IEEE Transactions on Electron Devices, vol. ED-35, no. 7, p. 1063 - 1070, July 1988.
5. J. Lee, C. Hegarty and C. Hu, "Electrical Characteristics of MOSFET's Using Low-Pressure Chemical Vapor Deposited Oxide," IEEE Electron Device Letters, vol. EDL-9, no. 7, p. 324 - 327, July 1988.
6. J. Lee, I-C Chen and C. Hu, "Modeling and Characterization of Gate Oxide Reliability," Special Issue of IEEE Transactions on Electron Devices on Reliability, Vol. ED-35, no. 12, p. 2268 - 2278, December 1988.
7. H. Hwang, W. Ting, D. L. Kwong, J. Lee, L. Buhrow and R. Bowling, "Electrical Characteristics of Reoxidized-nitrided CVD Oxide," Applied Physics Letters, 55(8), p. 755 - 756, 21 August, 1989.
8. R. Moazzami, J. Lee and C. Hu, "Temperature Acceleration of Time-Dependent Dielectric Breakdown," Special issue of IEEE Transactions on Electron Devices on Vacuum Microelectronic Devices, vol. ED-36, no. 11, p. 2462 - 2465, November 1989.
9. H. Hwang, W. Ting, D.L. Kwong, J. Lee, L. Buhrow and R.A. Bowling, "Effects of Dynamic Stressing on Nitrided and Reoxidized-Nitrided Chemical Vapor Deposited Gate Oxides," IEEE Electron Device Letters, vol. EDL-10, no. 12, p. 568 - 570, December 1989.
10. J. Lin, S. Banerjee, J. Lee, and C. Teng, "Soft Breakdown in Titanium-Silicided Shallow Source/Drain Junction," IEEE Electron Device Letters, vol. EDL-11, no. 5, p. 191 - 193, May 1990.
11. K. Park, S. Batra, J. Lin, S. Yoganathan, J. Lee, S. Banerjee, S. Sun, J. Yeargain, and G. Lux, "Anomalous Capacitance-Voltage Behavior Due to Dopant Segregation and

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- Carrier Trapping in Arsenic-Implanted Polysilicon and Polycide Gates," Applied Physics Letters, vol. 56, no. 23, p.2325 - 2327, June 4, 1990.
12. J. Lin, S. Banerjee, J. Lee, and C. Teng, "Anomalous Current-Voltage Behavior in Titanium-Silicided Source/Drain Junctions," Journal of Applied Physics, vol. 68, no. 3, p. 1082 - 1087, August 1, 1990.
 13. H. Hwang, W. Ting, B. Maiti, D.L. Kwong and J. Lee, "Electrical Characteristics of Ultrathin Gate Dielectrics Prepared by Rapid Thermal Oxidation of Si in N₂O," Applied Physics Letters, vol. 57, no. 10, p. 1010 - 1011, Sept. 3, 1990.
 14. S. Batra, K. Park, J. Lin, S. Yoganathan, J. Lee, S. Banerjee, S. Sun, J. Yeargain and G. Lux "Effects of Dopant Redistribution, Segregation and Carrier Trapping in As-Implanted MOS Gates," IEEE Transactions on Electron Devices, vol. 37, no. 11, p. 2322 - 2330, October, 1990.
 15. S. Bhattacharya, S. Banerjee, J. Lee, A. Tasch and A. Chatterjee, "The Impact of Trench Isolation on Latch-up Immunity in Bulk, Non-epitaxial CMOS," IEEE Electron Device Letters, vol. EDL-12, no. 2, p. 77 - 79, February, 1991.
 16. W. Ting, H. Hwang, J. Lee and D. L. Kwong, "Composition and Growth Kinetics of Ultrathin SiO₂ Films Formed by Oxidizing Si Substrate in N₂O," Applied Physics Letters, vol. 57, p. 2808 - 2810, 1990.
 17. W. Ting, P.C. Li, G. Q. Lo, J. Lee and D.L. Kwong, "Metal-Oxide Semiconductor Characteristics of Rapid Thermal Processed Chemical Vapor Deposited SiO₂ Gate Dielectrics," Solid State Electronics , vol. 34, no. 4, p 385 - 388, 1991.
 18. W. Ting, H. Hwang, J. Lee and D.L. Kwong, "Growth Kinetics of Ultrathin SiO₂ Films Prepared by Rapid Thermal Oxidation of Si Substrates in N₂O," Journal of Applied Physics, vol. 70, no. 2, p. 1072 - 1074, July 15, 1991.
 19. J. Lin, K. Park, S. Batra, S. Banerjee, J. Lee and G. Lux, "Enhancement of Boron Diffusion Through Gate Oxides in MOS Devices During Rapid Thermal Silicidation," Applied Physics Letters, vol. 58, no. 19, p. 2123 - 2125, May 1991.
 20. H. Hwang, W. Ting, D. L. Kwong and J. Lee, "A Physical Model for Boron Penetration Through Oxynitride Gate Dielectric Prepared by Rapid Thermal Processing in N₂O," Applied Physics Letters, vol. 59, no. 13, p. 1581 - 1582, September 23, 1991.
 21. H. Hwang, W. Ting, D. L. Kwong and J. Lee, "Improved Reliability Characteristics of Submicron nMOSFET's with Oxynitride Gate Dielectrics Prepared by Rapid Thermal Oxidation in N₂O," IEEE Electron Device Letters, vol. 12, no.9, p.495-497, September 1991.

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